D1NK80Z-VB TO252 Datasheet

N-Channel 800V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	800	
$R_{DS(on)}$ typ. (Ω) at 25 °C	V_{GS} = 10 V	2.38
Q_g max. (nC)	90	
Q_{gs} (nC)	11	
Q_{gd} (nC)	19	
Configuration	Single	

FEATURES

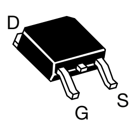
- Low figure-of-merit (FOM) R_{on} x Q_g
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)

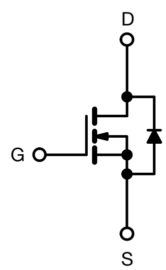
RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Renewable energy
  - Solar (PV inverters)

DPAK
(TO-252)





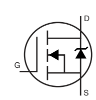
N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)						
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	800	V
Gate-source voltage			V_{GS}	± 30	V
Continuous drain current (T_J = 150 °C)	V_{GS} at 10 V	T_C = 25 °C	I_D	2.8	A
		T_C = 100 °C		1.8	
Pulsed drain current [a]			I_{DM}	5	A
Linear derating factor				0.5	W/°C
Single pulse avalanche energy [b]			E_{AS}	14	mJ
Maximum power dissipation			P_D	62.5	W
Operating junction and storage temperature range			T_J, T_{stg}	-55 to +150	°C
Drain-source voltage slope	T_J = 125 °C		dV/dt	70	V/ns
Reverse diode dV/dt [d]				0.13	
Soldering recommendations (peak temperature) [c]	For 10 s			300	°C

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature
b. V_{DD} = 140 V, starting T_J = 25 °C, L = 28.2 mH, R_g = 25 Ω, I_{AS} = 0.9 A
c. 1.6 mm from case
d. $I_{SD} \le I_D$, dI/dt = 100 A/μs, starting T_J = 25 °C

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	2.0	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA	800	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA	-	1.0	-	V/°C
Gate-source threshold Voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2.0	-	4.0	V
Gate-source leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
		V_{GS} = ± 30 V	-	-	± 1	μA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 800 V, V_{GS} = 0 V	-	-	1	μA
		V_{DS} = 640 V, V_{GS} = 0 V, T_J = 125 °C	-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 1.0 A	-	2.38	-	Ω
Forward transconductance	g_{fs}	V_{DS} = 30 V, I_D = 1.0 A	-	1.0	-	S
Dynamic						
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 100 V, f = 1 MHz	-	315	-	pF
Output capacitance	C_{oss}		-	20	-	
Reverse transfer capacitance	C_{rss}		-	6	-	
Effective output capacitance, energy related [a]	$C_{o(er)}$	V_{DS} = 0 V to 480 V, V_{GS} = 0 V	-	13	-	
Effective output capacitance, time related [b]	$C_{o(tr)}$		-	45	-	
Total gate charge	Q_g	V_{GS} = 10 V, I_D = 1.0 A, V_{DS} = 480 V	-	9.8	19.6	nC
Gate-source charge	Q_{gs}		-	2.4	-	
Gate-drain charge	Q_{gd}		-	3.9	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 480 V, I_D = 1.0 A, V_{GS} = 10 V, R_g = 9.1 Ω	-	11	22	ns
Rise time	t_r		-	7	14	
Turn-off delay time	$t_{d(off)}$		-	19	38	
Fall time	t_f		-	27	54	
Gate input resistance	R_g	f = 1 MHz, open drain	1.8	3.6	7.2	Ω
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	2.8	A
Pulsed diode forward current	I_{SM}		-	-	5	
Diode forward voltage	V_{SD}	T_J = 25 °C, I_S = 11 A, V_{GS} = 0 V	-	-	1.2	V
Reverse recovery time	t_{rr}	T_J = 25 °C, I_F = I_S = 1.0 A, dI/dt = 100 A/μs, V_R = 25 V	-	278	556	ns
Reverse recovery charge	Q_{rr}		-	0.9	1.8	μC
Reverse recovery current	I_{RRM}		-	5	-	A

Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

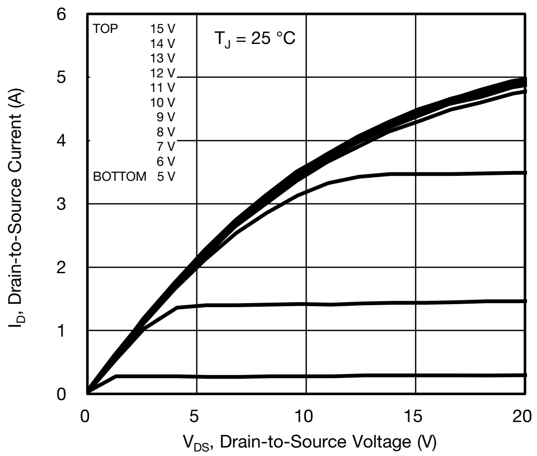


Fig. 1 - Typical Output Characteristics

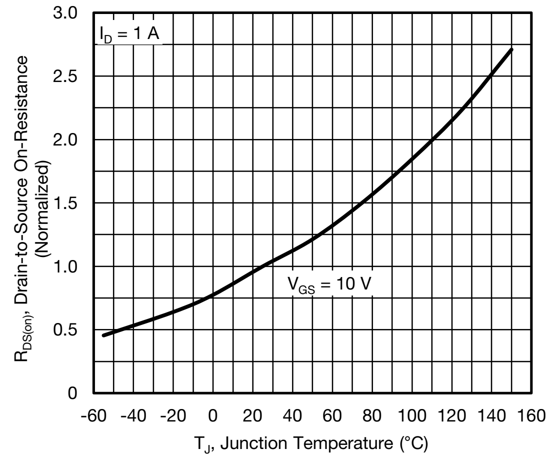


Fig. 4 - Normalized On-Resistance vs. Temperature

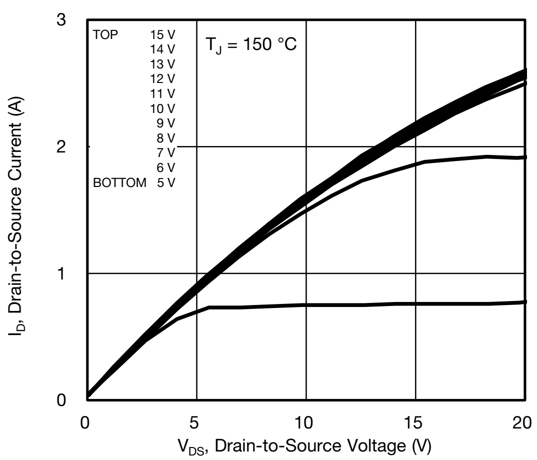


Fig. 2 - Typical Output Characteristics

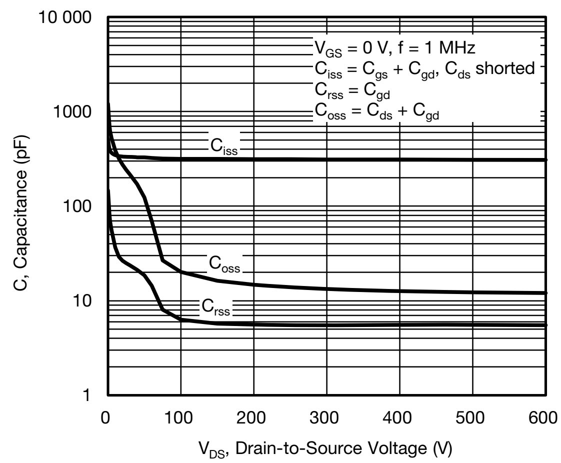


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

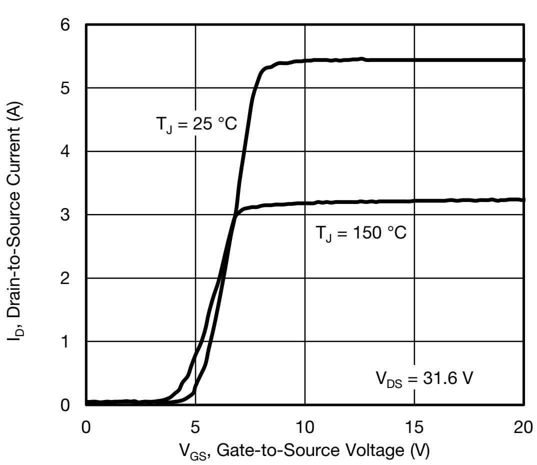


Fig. 3 - Typical Transfer Characteristics

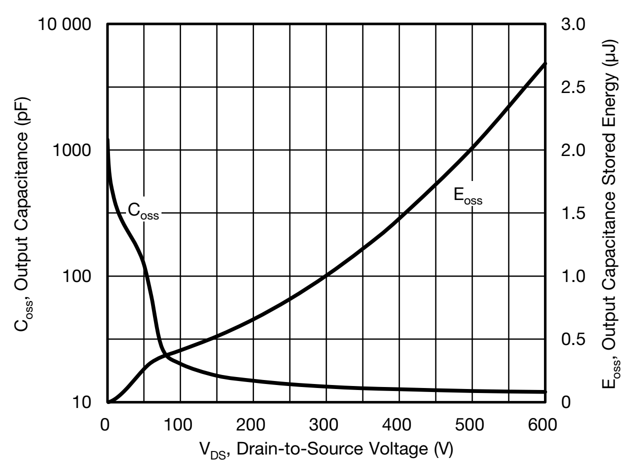


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

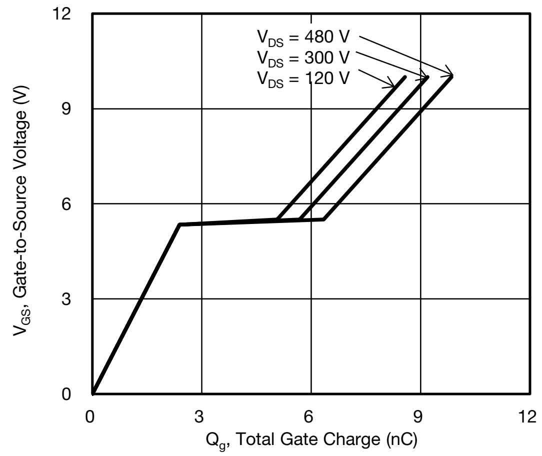


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

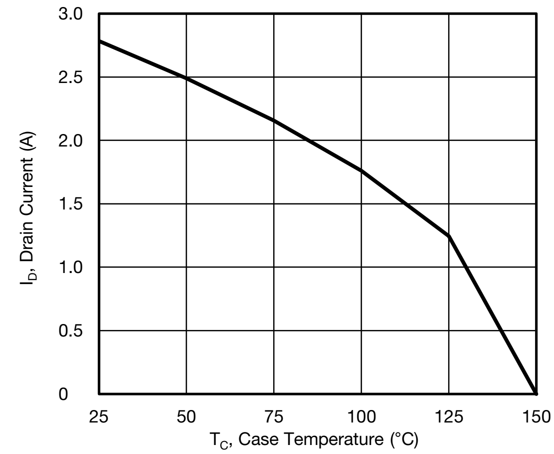


Fig. 10 - Maximum Drain Current vs. Case Temperature

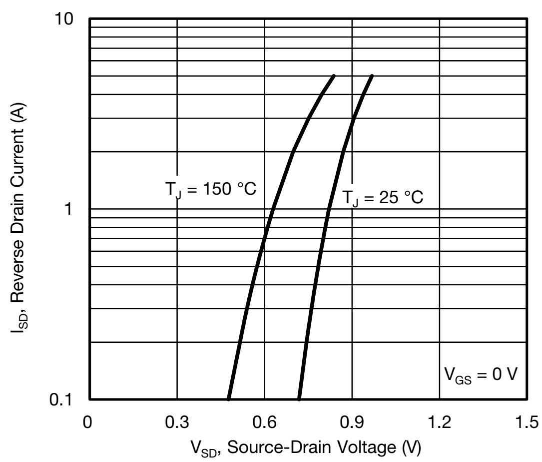


Fig. 8 - Typical Source-Drain Diode Forward Voltage

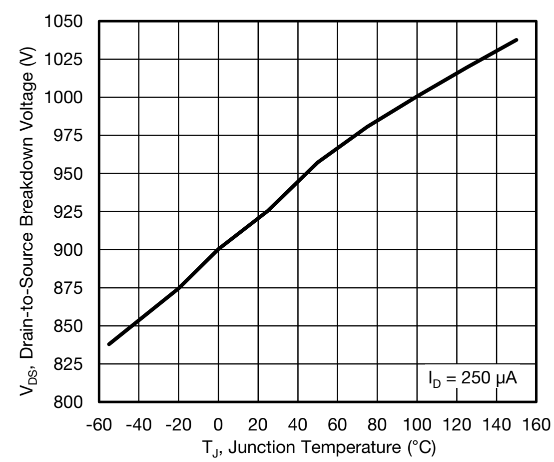
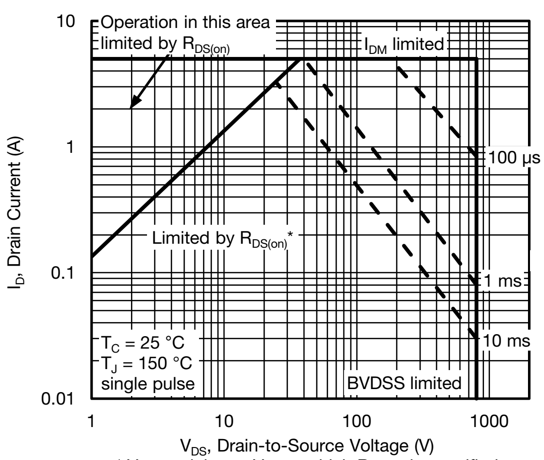


Fig. 11 - Temperature vs. Drain-to-Source Voltage



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Fig. 9 - Maximum Safe Operating Area

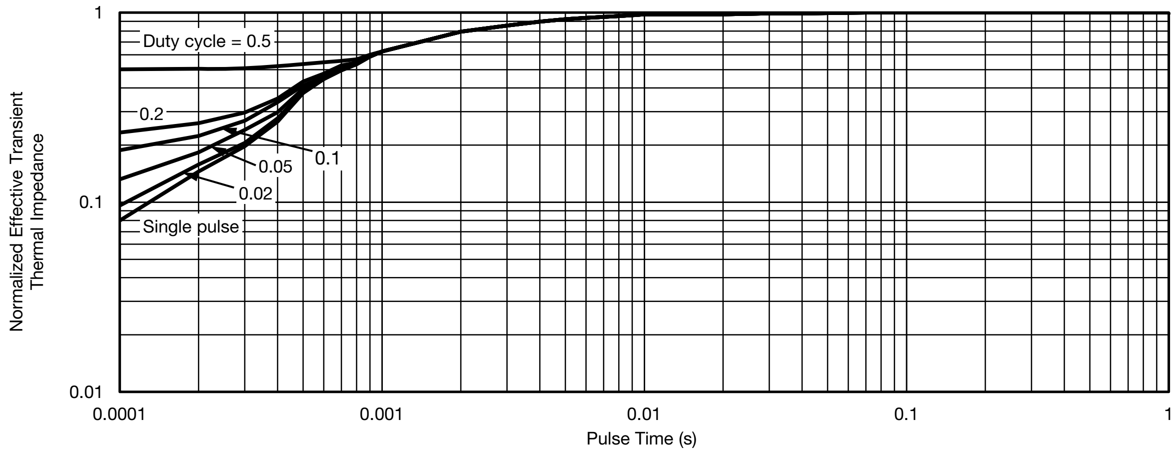


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

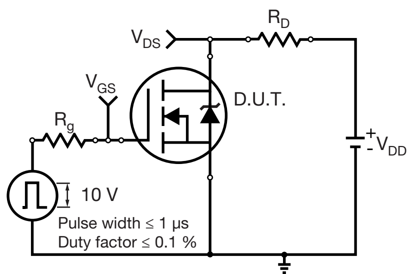


Fig. 13 - Switching Time Test Circuit

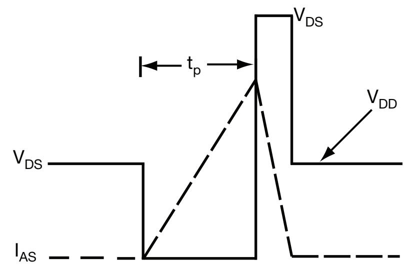


Fig. 16 - Unclamped Inductive Waveforms

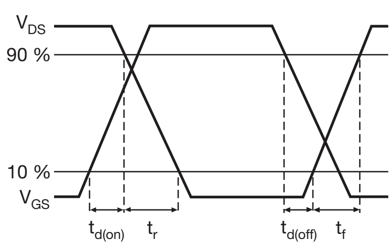


Fig. 14 - Switching Time Waveforms

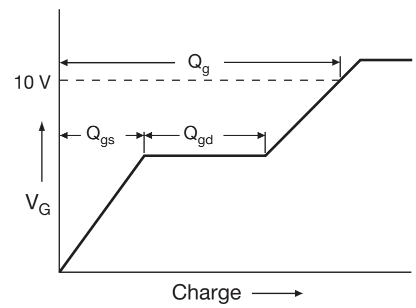


Fig. 17 - Basic Gate Charge Waveform

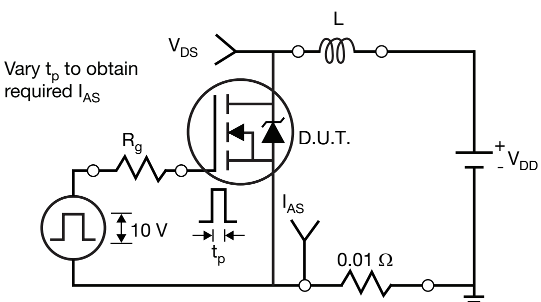


Fig. 15 - Unclamped Inductive Test Circuit

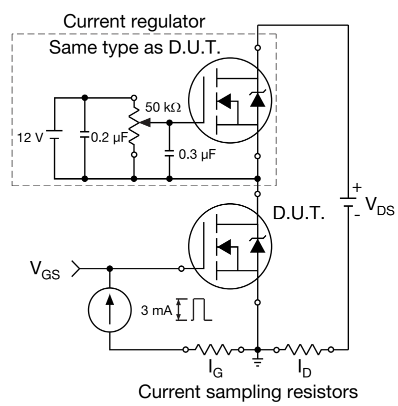
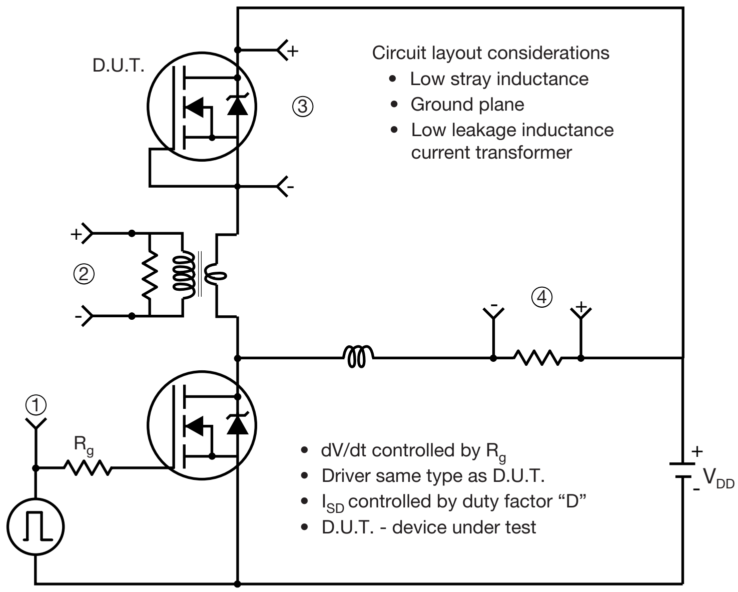
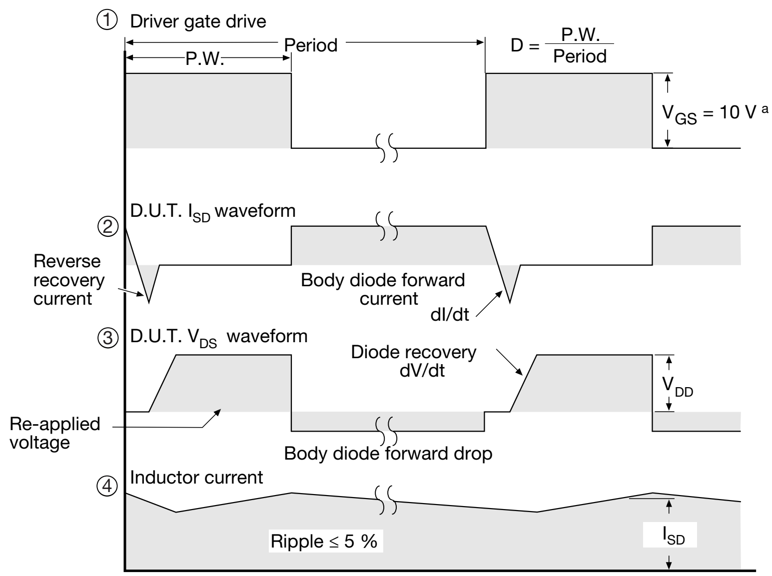


Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit





Note

a. V_{GS} = 5 V for logic level devices

Fig. 19 - For N-Channel

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